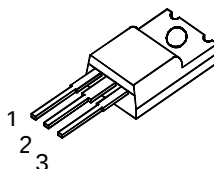


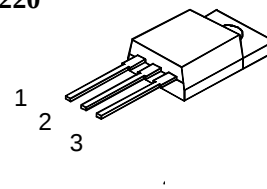
1. FEATURES:

- High Voltage Capability
- High Speed Switching
- Wide SOA

TO-220F



TO-220



2. APPLICATION:

1:B 2:C 3:E

- Fluorescent Lamp
- Electronic Ballast
- Switch mode power supply
- Electronic Transformer

3. ABSOLUTE MAXIMUM RATINGS(Ta=25℃,unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	700	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	I_C	8	A
Collector Power Dissipation	P_C	100	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55~150	℃

4. ELECTRICAL CHARACTERISTICS(Ta=25℃ Unless Otherwise Specified)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=1mA$ $I_E=0$	700		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10mA$ $I_B=0$	400		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1mA$ $I_C=0$	9		V
Collector-Base Cutoff Current	I_{CBO}	$V_{CB}=680V$ $I_E=0$		5	uA
Collector-Emitter Cutoff Current	I_{CEO}	$V_{CE}=390V$ $I_B=0$		5	uA
Emitter-Base Cutoff Current	I_{EBO}	$V_{EB}=9V$ $I_C=0$		5	uA
Collector-Emitter Saturation Voltage	V_{CEsat}	$I_C=2A$ $I_B=0.4A$		1.0	V
		$I_C=8A$ $I_B=2A$		2.5	V
Base-Emitter Saturation Voltage	V_{BEsat}	$I_C=5A$ $I_B=1A$		1.8	V
DC Current Gain	h_{FE}	$V_{CE}=5V$ $I_C=2A$	15	40	
Falling Time	t_f	$I_C=0.5A$		0.5	us
Storage Time	t_s	$I_{B1}=-I_{B2}=0.1A$		8	us
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=500mA$ $f=1MHz$	5		MHz

REV:A

Mar-06

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